

# PZT222AT1

Preferred Device

## NPN Silicon Planar Epitaxial Transistor

This NPN Silicon Epitaxial transistor is designed for use in linear and switching applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

### Features

- PNP Complement is PZT2907AT1
- The SOT-223 package can be soldered using wave or reflow
- SOT-223 package ensures level mounting, resulting in improved thermal conduction, and allows visual inspection of soldered joints
- The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Available in 12 mm tape and reel
- Pb-Free Packages are Available

### MAXIMUM RATINGS

| Rating   | Symbol    | Value        | Unit             |
|--|-----------|--------------|------------------|
| Collector-Emitter Voltage  | $V_{CEO}$ | 40           | Vdc              |
| Collector-Base Voltage   | $V_{CBO}$ | 75           | Vdc              |
| Emitter-Base Voltage<br>(Open Collector)                           | $V_{EBO}$ | 6.0          | Vdc              |
| Collector Current  | $I_C$     | 600          | mA <sub>dc</sub> |
| Total Power Dissipation<br>up to $T_A = 25^\circ\text{C}$ (Note 1) | $P_D$     | 1.5          | W                |
| Storage Temperature Range  | $T_{stg}$ | - 65 to +150 | $^\circ\text{C}$ |
| Junction Temperature   | $T_J$     | 150          | $^\circ\text{C}$ |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Device mounted on an epoxy printed circuit board 1.575 inches x 1.575 inches x 0.059 inches; mounting pad for the collector lead min. 0.93 inches<sup>2</sup>.

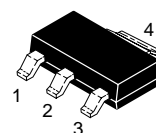
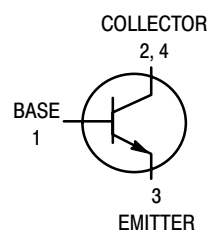
### THERMAL CHARACTERISTICS

| Rating  | Symbol          | Value     | Unit                      |
|---|-----------------|-----------|---------------------------|
| Thermal Resistance,<br>Junction-to-Ambient                                  | $R_{\theta JA}$ | 83.3      | $^\circ\text{C}/\text{W}$ |
| Lead Temperature for Soldering,<br>0.0625" from case<br>Time in Solder Bath | $T_L$           | 260<br>10 | $^\circ\text{C}$<br>Sec   |



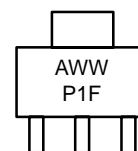
ON Semiconductor®

### SOT-223 PACKAGE NPN SILICON TRANSISTOR SURFACE MOUNT



SOT-223 (TO-261)  
CASE 318E-04  
STYLE 1

### MARKING DIAGRAM



A = Assembly Location  
WW = Work Week

### ORDERING INFORMATION

| Device     | Package              | Shipping†          |
|------------|----------------------|--------------------|
| PZT222AT1  | SOT-223              | 3000 Tape & Reel   |
| PZT222AT1G | SOT-223<br>(Pb-Free) | 3000 Tape & Reel   |
| PZT222AT3  | SOT-223              | 10,000 Tape & Reel |
| PZT222AT3G | SOT-223<br>(Pb-Free) | 10,000 Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# PZT2222AT1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic  | Symbol               | Min    | Max      | Unit         |
|---|----------------------|--------|----------|--------------|
| <b>OFF CHARACTERISTICS</b>  |                      |        |          |              |
| Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)  | V <sub>(BR)CEO</sub> | 40     | –        | Vdc          |
| Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)   | V <sub>(BR)CBO</sub> | 75     | –        | Vdc          |
| Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)   | V <sub>(BR)EBO</sub> | 6.0    | –        | Vdc          |
| Base-Emitter Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>BE</sub> = – 3.0 Vdc)   | I <sub>BEX</sub>     | –      | 20       | nAdc         |
| Collector-Emitter Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>BE</sub> = – 3.0 Vdc)  | I <sub>CEX</sub>     | –      | 10       | nAdc         |
| Emitter-Base Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)   | I <sub>EBO</sub>     | –      | 100      | nAdc         |
| Collector-Base Cutoff Current<br>(V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0)<br>(V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 125°C) | I <sub>CBO</sub>     | –<br>– | 10<br>10 | nAdc<br>μAdc |

## ON CHARACTERISTICS

|  |                      |   |  |       |
|--|----------------------|---|--|-------|
| DC Current Gain<br>(I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub> = 10 Vdc)<br>(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc)<br>(I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc)<br>(I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, T <sub>A</sub> = – 55°C)<br>(I <sub>C</sub> = 150 mAdc, V <sub>CE</sub> = 10 Vdc)<br>(I <sub>C</sub> = 150 mAdc, V <sub>CE</sub> = 1.0 Vdc)<br>(I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc) | h <sub>FE</sub>      | 35<br>50<br>70<br>35<br>100<br>50<br>40 | –<br>–<br>–<br>–<br>300<br>–<br>–            | –     |
| Collector-Emitter Saturation Voltages<br>(I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)<br>(I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)  | V <sub>CE(sat)</sub> | –<br>–                                  | 0.3<br>1.0                                   | Vdc   |
| Base-Emitter Saturation Voltages<br>(I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)<br>(I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)   | V <sub>BE(sat)</sub> | 0.6<br>–                                | 1.2<br>2.0                                   | Vdc   |
| Input Impedance<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 10 mAdc, f = 1.0 kHz)   | h <sub>ie</sub>      | 2.0<br>0.25                             | 8.0<br>1.25                                  | kΩ    |
| Voltage Feedback Ratio<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 10 mAdc, f = 1.0 kHz)  | h <sub>re</sub>      | –<br>–                                  | 8.0x10 <sup>-4</sup><br>4.0x10 <sup>-4</sup> | –     |
| Small-Signal Current Gain<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 10 mAdc, f = 1.0 kHz)   | h <sub>fe</sub>      | 50<br>75                                | 300<br>375                                   | –     |
| Output Admittance<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)<br>(V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 10 mAdc, f = 1.0 kHz)   | h <sub>oe</sub>      | 5.0<br>25                               | 35<br>200                                    | μmhos |
| Noise Figure (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 100 μAdc, f = 1.0 kHz)  | F                    | –                                       | 4.0  | dB    |

## DYNAMIC CHARACTERISTICS

|   |                |     |     |     |
|---|----------------|-----|-----|-----|
| Current-Gain – Bandwidth Product<br>(I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz) | f <sub>T</sub> | 300 | –   | MHz |
| Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)                        | C <sub>c</sub> | –   | 8.0 | pF  |
| Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)                        | C <sub>e</sub> | –   | 25  | pF  |

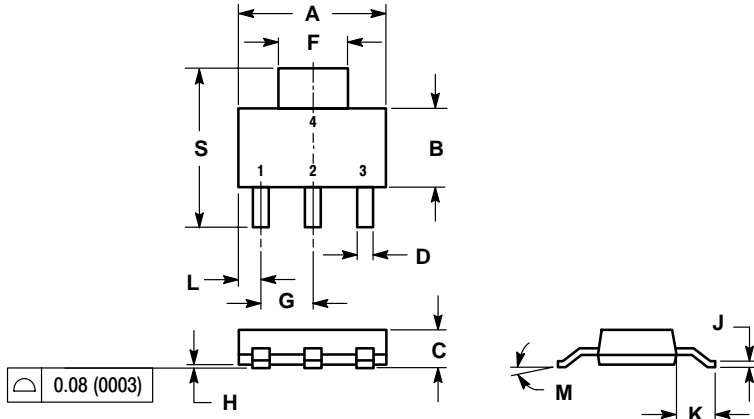
## SWITCHING TIMES (T<sub>A</sub> = 25°C)

|              |  |                |   |     |    |
|--------------|--|----------------|---|-----|----|
| Delay Time   | (V <sub>CC</sub> = 30 Vdc, I <sub>C</sub> = 150 mAdc,<br>I <sub>B(on)</sub> = 15 mAdc, V <sub>EB(off)</sub> = 0.5 Vdc)<br>Figure 1 | t <sub>d</sub> | – | 10  | ns |
| Rise Time    |  | t <sub>r</sub> | – | 25  |    |
| Storage Time | (V <sub>CC</sub> = 30 Vdc, I <sub>C</sub> = 150 mAdc,<br>I <sub>B(on)</sub> = I <sub>B(off)</sub> = 15 mAdc)<br>Figure 2           | t <sub>s</sub> | – | 225 | ns |
| Fall Time    |  | t <sub>f</sub> | – | 60  |    |

# PZT2222AT1

## PACKAGE DIMENSIONS

SOT-223 (TO-261)  
CASE 318E-04  
ISSUE K



NOTES:

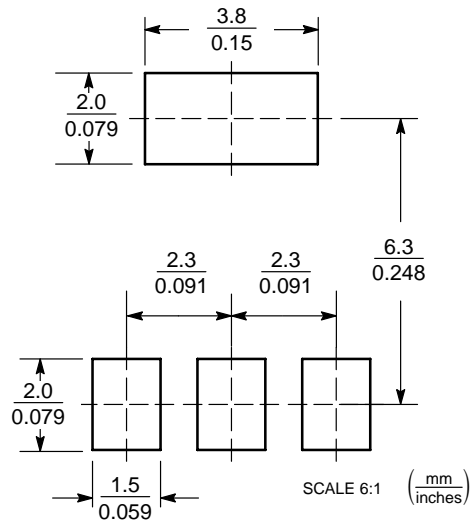
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES |        | MILLIMETERS |       |
|-----|--------|--------|-------------|-------|
|     | MIN    | MAX    | MIN         | MAX   |
| A   | 0.249  | 0.263  | 6.30        | 6.70  |
| B   | 0.130  | 0.145  | 3.30        | 3.70  |
| C   | 0.060  | 0.068  | 1.50        | 1.75  |
| D   | 0.024  | 0.035  | 0.60        | 0.89  |
| F   | 0.115  | 0.126  | 2.90        | 3.20  |
| G   | 0.087  | 0.094  | 2.20        | 2.40  |
| H   | 0.0008 | 0.0040 | 0.020       | 0.100 |
| J   | 0.009  | 0.014  | 0.24        | 0.35  |
| K   | 0.060  | 0.078  | 1.50        | 2.00  |
| L   | 0.033  | 0.041  | 0.85        | 1.05  |
| M   | 0°     | 10°    | 0°          | 10°   |
| S   | 0.264  | 0.287  | 6.70        | 7.30  |

STYLE 1:

- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.